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Kind regards,

Team Nexperia



# **NUP1301**

# Ultra low capacitance ESD protection array Rev. 01 — 11 May 2009

**Product data sheet** 

### **Product profile**

#### 1.1 General description

Ultra low capacitance ElectroStatic Discharge (ESD) protection array in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package designed to protect one signal line in rail-to-rail configuration from the damage caused by ESD and other transients.

#### 1.2 Features

- ESD protection of one signal line (rail-to-rail configuration)
- Ultra low diode capacitance: C<sub>d</sub> = 0.6 pF
- Very low reverse leakage current: ≤ 30 nA
- ESD protection up to 30 kV
- IEC 61000-4-2; level 4 (ESD)
- IEC 61000-4-5 (surge);  $I_{PP}$  = 11 A at  $t_p$  = 8/20 μs
- AEC-Q101 qualified

#### 1.3 Applications

- Telecommunication networks
- Video line protection
- Microcontroller protection
- I<sup>2</sup>C-bus protection
- Antenna power supply
- Analog audio
- Class-D amplifier

#### 1.4 Quick reference data

Table 1. Quick reference data

T<sub>amb</sub> = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per diode						
$V_{RRM}$	repetitive peak reverse voltage		-	-	80	V
C <sub>d</sub>	diode capacitance	f = 1 MHz; $V_R = 0 V$	-	0.6	0.75	pF
I <sub>R</sub>	reverse current	$V_{R} = 80 \text{ V}$	-	-	100	nA



#### **Ultra low capacitance ESD protection array**

# 2. Pinning information

Table 2. Pinning

	;	9		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND	ground		
2	$V_{CC}$	supply voltage	3	3
3	I/O	input/output	1 2	1 2 006aaa763

# 3. Ordering information

Table 3. Ordering information

Type number	Package			
	Name	Description	Version	
NUP1301	-	plastic surface-mounted package; 3 leads	SOT23	

## 4. Marking

Table 4. Marking

Type number	Marking code <sup>[1]</sup>
NUP1301	LJ*

<sup>[1] \* = -:</sup> made in Hong Kong

# 5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per diode					
$V_{RRM}$	repetitive peak reverse voltage		-	80	V
$V_R$	reverse voltage		-	80	V
I <sub>F</sub>	forward current		<u>[1]</u> _	215	mA
I <sub>FRM</sub>	repetitive peak forward current	$t_p \leq 1 \text{ ms; } \delta \leq 0.25$	-	500	mA

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<sup>\* =</sup> p: made in Hong Kong

<sup>\* =</sup> t: made in Malaysia

<sup>\* =</sup> W: made in China

#### Ultra low capacitance ESD protection array

 Table 5.
 Limiting values ...continued

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$I_{FSM}$	non-repetitive peak	square wave	<u>[2]</u>		
	forward current	t <sub>p</sub> = 1 μs	-	4	Α
	$t_p = 1 \text{ ms}$	-	1	Α	
	$t_p = 1 s$	-	0.5	Α	
Per device					
$P_{PP}$	peak pulse power	$t_p = 8/20 \ \mu s$	[3][4]	220	W
$I_{PP}$	peak pulse current	$t_p = 8/20 \ \mu s$	[3][4]	11	Α
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	<u>[5][6]</u> _	250	mW
T <sub>j</sub>	junction temperature		-	150	°C
T <sub>amb</sub>	ambient temperature		<b>–55</b>	+150	°C
T <sub>stg</sub>	storage temperature		-65	+150	°C

<sup>[1]</sup> Pulse test:  $t_p \le 300 \ \mu s; \ \delta \le 0.02$ .

Table 6. ESD maximum ratings

Symbol	Parameter	Conditions	М	in Max	Unit
V <sub>ESD</sub> electrostatic discharge voltage	•	IEC 61000-4-2 (contact discharge)	[1][2]	30	kV
		machine model	-	400	V
	MIL-STD-883 (human body model)	-	10	kV	

<sup>[1]</sup> Device stressed with ten non-repetitive ESD pulses.

Table 7. ESD standards compliance

Standard	Conditions
IEC 61000-4-2; level 4 (ESD)	> 15 kV (air); > 8 kV (contact)
MIL-STD-883; class 3B (human body model)	> 8 kV

<sup>[2]</sup>  $T_i = 25$  °C prior to surge.

<sup>[3]</sup> Non-repetitive current pulse 8/20 µs exponential decay waveform according to IEC 61000-4-5.

<sup>[4]</sup> Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

<sup>[5]</sup> Single diode loaded.

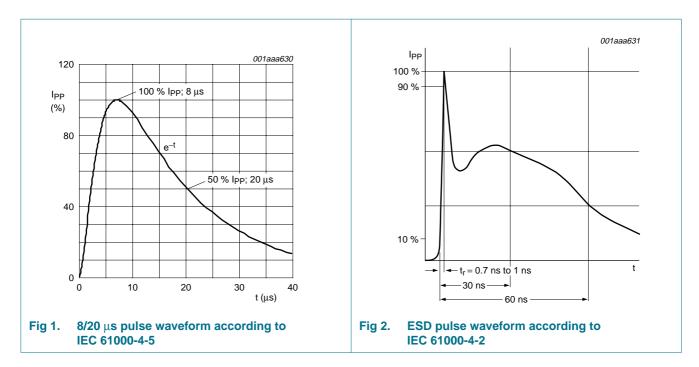
<sup>[6]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

<sup>[2]</sup> Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

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#### **Ultra low capacitance ESD protection array**

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#### Thermal characteristics 6.

**Product data sheet** 

Table 8. **Thermal characteristics** 

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per devic	<b>e</b>						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2]	-	-	500	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	360	K/W

<sup>[1]</sup> Single diode loaded.

Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

#### **Ultra low capacitance ESD protection array**

## 7. Characteristics

Table 9. Electrical characteristics

 $T_{amb}$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	М	in	Тур	Max	Unit
Per diod	9						
$V_{BR}$	breakdown voltage	$I_R = 100 \mu A$	10	00	-	-	V
V <sub>F</sub>	forward voltage		<u>[1]</u>				
		$I_F = 1 \text{ mA}$	-		-	715	mV
	$I_F = 10 \text{ mA}$	-		-	855	mV	
		$I_F = 50 \text{ mA}$	-		-	1	V
		$I_F = 150 \text{ mA}$	-		-	1.25	V
I <sub>R</sub>	reverse current						
		V <sub>R</sub> = 25 V	-		-	30	nA
		$V_{R} = 80 \text{ V}$	-		-	100	nA
		$V_R = 25 \text{ V};$ $T_j = 150 ^{\circ}\text{C}$	-		-	25	μΑ
		$V_R = 80 \text{ V};$ $T_j = 150 ^{\circ}\text{C}$	-		-	35	μΑ
C <sub>d</sub>	diode capacitance	$f = 1 MHz; V_R = 0 V$	-		0.6	0.75	pF
Per devi	ce						
V <sub>CL</sub>	clamping voltage	I <sub>PP</sub> = 1 A	[2][3]		-	3	V
		I <sub>PP</sub> = 11 A	[2][3]		-	20	V

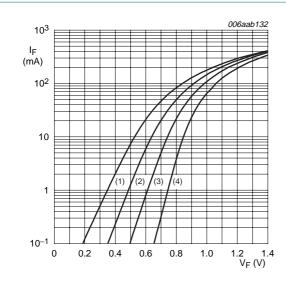
<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 

<sup>[2]</sup> Non-repetitive current pulse  $8/20~\mu s$  exponential decay waveform according to IEC 61000-4-5.

<sup>[3]</sup> Measured from pin 3 to pins 1 and 2 (pins 1 and 2 are connected).

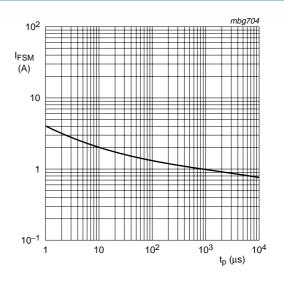
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#### Ultra low capacitance ESD protection array



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

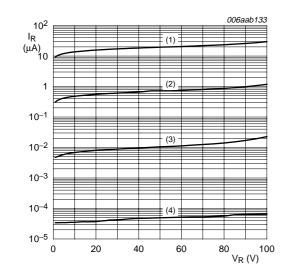
Fig 3. Forward current as a function of forward voltage; typical values



Based on square wave currents.

 $T_i = 25$  °C; prior to surge

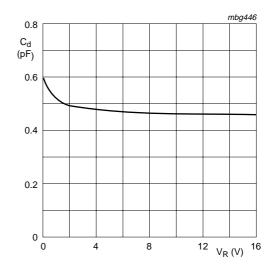
Non-repetitive peak forward current as a Fig 4. function of pulse duration; typical values



- (1)  $T_{amb} = 150 \, ^{\circ}C$
- (2)  $T_{amb} = 85 \, ^{\circ}C$
- (3)  $T_{amb} = 25 \, ^{\circ}C$
- (4)  $T_{amb} = -40 \, ^{\circ}C$

**Product data sheet** 

Fig 5. Reverse current as a function of reverse voltage; typical values



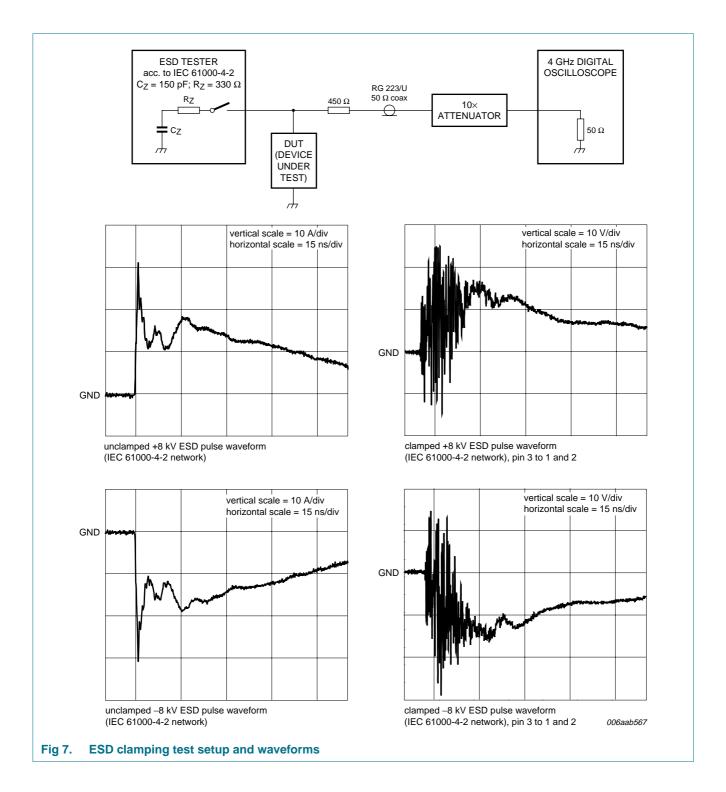
 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz$ 

Fig 6. Diode capacitance as a function of reverse voltage; typical values

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#### **Ultra low capacitance ESD protection array**

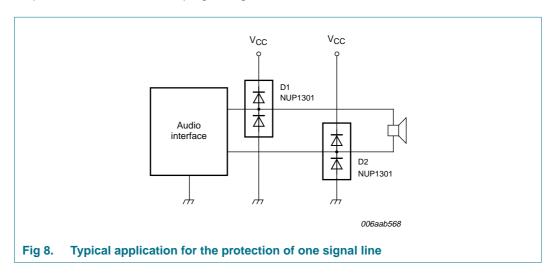


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**Ultra low capacitance ESD protection array** 

## 8. Application information

Protection of a single (high-speed) data line in rail-to-rail configuration. The protected data line is connected to pin 3. Pin 1 is connected to ground (GND) and pin 2 is connected to the supply rail (supply voltage  $V_{CC}$ .) When the transient voltage exceeds the forward voltage drop of one diode, the transient is directed either to the supply rail or to GND. The advantages of these solutions are: low line capacitance (0.6 pF typically), fast response time, and low clamping voltage.



#### Circuit board layout and protection device placement:

Circuit board layout is critical for the suppression of ESD, Electrical Fast Transient (EFT) and surge transients. The following guidelines are recommended:

- 1. Place the NUP1301 as close to the input terminal or connector as possible.
- 2. The path length between the NUP1301 and the protected line should be minimized.
- 3. Keep parallel signal paths to a minimum.
- 4. Avoid running protected conductors in parallel with unprotected conductors.
- 5. Minimize all Printed-Circuit Board (PCB) conductive loops including power and ground loops.
- 6. Minimize the length of the transient return path to ground.
- 7. Avoid using shared transient return paths to a common ground point.
- 8. Ground planes should be used whenever possible. For multilayer PCBs, use ground vias.

#### 9. Test information

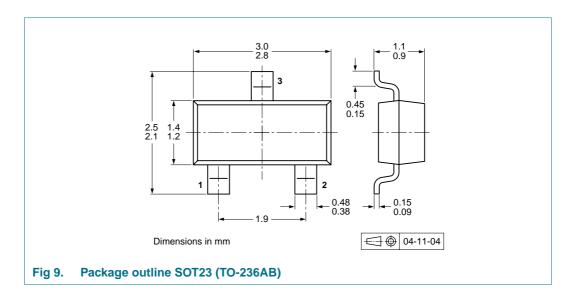
#### 9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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#### **Ultra low capacitance ESD protection array**

# 10. Package outline



# 11. Packing information

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Table 10. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

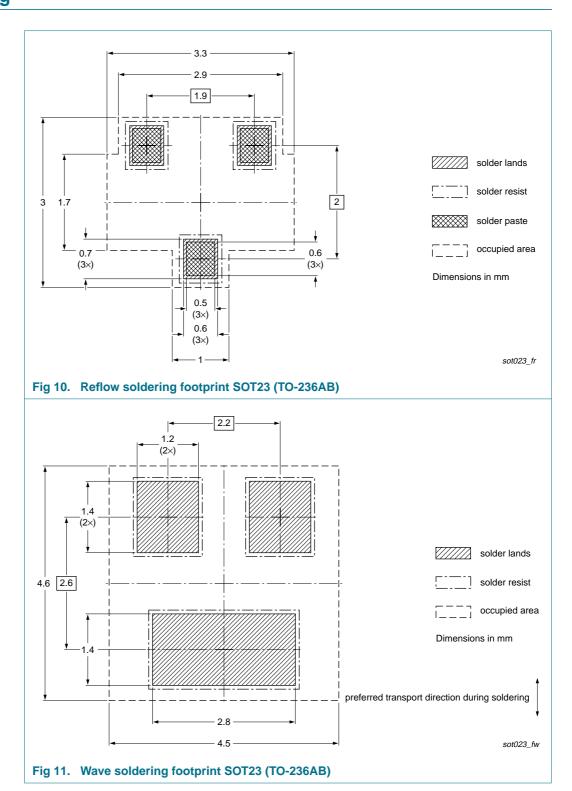
Type number	Package	Description	Packing	Packing quantity	
			3000	10000	
NUP1301	SOT23	4 mm pitch, 8 mm tape and reel	-215	-235	

<sup>[1]</sup> For further information and the availability of packing methods, see Section 15.

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#### **Ultra low capacitance ESD protection array**

## 12. Soldering



## Ultra low capacitance ESD protection array

# 13. Revision history

#### Table 11. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NUP1301_1	20090511	Product data sheet	-	-

#### **Ultra low capacitance ESD protection array**

## 14. Legal information

#### 14.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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#### **Ultra low capacitance ESD protection array**

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